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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	ATTORNEY DOCKET NO. CONFIRMATION NO. 303.455US3 5953	
09/470,265	12/22/1999	KARL M ROBINSON	303.455US3		
21186 . 75	90 09/25/2003				
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.			EXAMINER		
P.O. BOX 2938 MINNĒAPOLI			TRAN, THIEN F		
\$ -			ART UNIT	PAPER NUMBER	
			2811		

DATE MAILED: 09/25/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

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•	Application No.	7	Applicant(s)	
Office A - 4' - 1 O	09/470,265	F	ROBINSON, KARL M	M
Offic Action Summary	Examiner	-	Art Unit	
	Thien Tran		2811	
The MAILING DATE of this communication app Period for Reply	ears on the cover	sheet with the cor	respondence addres	:S
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w. - Failure to reply within the set or extended period for reply will, by statute, - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, howe within the statutory min vill apply and will expire s cause the application to	ver, may a reply be timely imum of thirty (30) days w SIX (6) MONTHS from the become ABANDONED	y filed vill be considered timely. e mailing date of this commu (35 U.S.C. § 133).	nication.
Status				
1) Responsive to communication(s) filed on		1		
, <u> </u>	is action is non-fi			
3) Since this application is in condition for allowal closed in accordance with the practice under a Disposition of Claims				ents is
4)⊠ Claim(s) <u>19,20,53,79-87,98-102 and 104-124</u>	is/are pending in	the application.		
4a) Of the above claim(s) <u>80,83,86,98-102,104</u>			from consideration.	
5) Claim(s) is/are allowed.				
6) Claim(s) 19,20,53,79,81,82,84,85,87 and 107-	112 is/are rejecte	d.		
7) Claim(s) is/are objected to.				
8) Claim(s) are subject to restriction and/or	r election require	ment.	•	
Application Papers				
9) The specification is objected to by the Examiner				
10) ☐ The drawing(s) filed on is/are: a) ☐ accep	•	-		
Applicant may not request that any objection to the		*	, ,	
11) The proposed drawing correction filed on		-	ed by the Examiner.	
If approved, corrected drawings are required in rep 12) The oath or declaration is objected to by the Exa	•	ion.		
,	ammen.			
Priority under 35 U.S.C. §§ 119 and 120			4 D 40	
13) Acknowledgment is made of a claim for foreign	i prionty under 35	U.S.C. § 119(a)-	(a) or (t).	
a) All b) Some * c) None of:	- h h			
1. Certified copies of the priority documents			, No	
2. Certified copies of the priority documents		• •		
 3. Copies of the certified copies of the prior application from the International But * See the attached detailed Office action for a list 	reau (PCT Rule 1	7.2(a)).	·	je
14) Acknowledgment is made of a claim for domestic	c priority under 3	5 U.S.C. § 119(e)	(to a provisional app	olication).
a) ☐ The translation of the foreign language pro 15)☐ Acknowledgment is made of a claim for domesti				
Attachment(s)	, -			
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 23	4)		PTO-413) Paper No(s) tent Application (PTO-15:	

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DETAILED ACTION

Claim Objections

Claim 108 is objected to because of the following informalities: lines 2-3, "the first conductive plate" should be --the first conductive capacitor plate--.

Appropriate correction is required.

Claim 110 is objected to because of the following informalities: lines 2-3, "the first conductive plate" should be --the first conductive capacitor plate--.

Appropriate correction is required.

Specification

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed, a device.

The following title is suggested: Devices having improved capacitance.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 19, 53, 79, 81, 85, 87, 108 and 112 are rejected under 35 U.S.C. 102(b) as being anticipated by Suguro et al. (USPN 5,189,503).

Suguro et al. discloses the claimed capacitor (Fig. 7d) comprising a first conductive capacitor plate 45 of W; a second conductive capacitor plate 51; a dielectric 47 interposed between said first and second conductive capacitor

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plates, wherein said dielectric is a metal oxide of WO₂ overlying the first conductive capacitor plate, wherein a metal layer includes a non-oxidized portion 45 and an oxidized portion 47, wherein the oxidized portion is the dielectric.

Regarding claims 79 and 85, the oxidized portion 47 of the metal layer comprises tungsten.

Regarding claims 81 and 87, the second conductive capacitor plate 51 is formed of metal.

Regarding claims 108 and 112, the capacitor further comprises a diffusion barrier layer (an upper portion of the layer 45 of tungsten) interposed between the first conductive capacitor plate (a lower portion of the layer 45 of tungsten) and the oxidized portion 47 of the metal layer.

Claims 19, 53, 79, 81, 85, 87, 107, 108, 111 and 112 are rejected under 35 U.S.C. 102(b) as being anticipated by Hirose (JP 7-226485).

Hirose discloses the claimed capacitor (Fig. 13) comprising a first conductive capacitor plate 13 of Ti; a second conductive capacitor plate 17; a dielectric 14A interposed between said first and second conductive capacitor plates, wherein said dielectric is an metal oxide layer of TiO₂ overlying the first conductive capacitor plate, wherein a metal layer of Ti includes a non-oxidized portion 13 and an oxidized portion, wherein the oxidized portion is the dielectric.

Regarding claims 79, 85, 107 and 111, the oxidized portion 14A of the metal layer comprises titanium.

Regarding claims 81 and 87, the second conductive capacitor plate 17 is formed of metal.

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Regarding claims 108 and 112, the capacitor further comprises a diffusion barrier layer 14 interposed between the first conductive capacitor plate 13 and the oxidized portion 14A of the metal layer.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 20, 82, 84 and 110 are rejected under 35 U.S.C. 103(a) as being unpatentable over Blodgett et al. (USPN 5,811,990) in view of Suguro et al. (USPN 5,189,503).

Blodgett et al. discloses a memory system 710 (Fig. 18) comprising a monolithic memory device 705 having dynamic random access memory device containing a capacitor; and a processor 710 used to generate external control signals which access the monolithic memory device 705 (col. 14, lines 10-15). Blodgett et al. does not explicitly disclose the capacitor comprising a first conductive capacitor plate, a second conductive capacitor plate, a metal oxide layer and a metal layer overlying the first conductive capacitor plate. Suguro et al. as described in details above discloses the capacitor as claimed. It would have been obvious to person having ordinary skill in the art at the time the invention was made to substitute the capacitor as taught by Suguro et al. for the capacitor in the memory system of Blodgett et al. in order to provide an improved

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capacitor with low current leakage. As a result, the modified Blodgett et al.

provides a capacitor comprising a first conductive capacitor plate formed of a first material; a second conductive capacitor plate; a metal oxide layer and a metal layer interposed between said first and second conductive capacitor plates.

Regarding claim 82, the oxidized portion of the metal layer comprises tungsten.

Regarding claim 84, the second conductive capacitor plate is formed of metal.

Regarding claim 110, the capacitor further comprises a diffusion barrier layer (an upper portion of layer 45 of tungsten) interposed between the first conductive capacitor plate (a lower portion of layer 45 of tungsten) and the oxidized portion 47 of the metal layer.

Claims 20, 82, 84, 109 and 110 are rejected under 35 U.S.C. 103(a) as being unpatentable over Blodgett et al. (USPN 5,811,990) in view of Hirose (JP 7-226485).

Blodgett et al. discloses a memory system 710 (Fig. 18) comprising a monolithic memory device 705 having dynamic random access memory device containing a capacitor; and a processor 710 used to generate external control signals which access the monolithic memory device 705 (col. 14, lines 10-15). Blodgett et al. does not explicitly disclose the capacitor comprising a first conductive capacitor plate, a second conductive capacitor plate, a metal oxide layer and a metal layer overlying the first conductive capacitor plate. Hirose as described in details above discloses the capacitor as claimed. It would have

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been obvious to person having ordinary skill in the art at the time the invention was made to substitute the capacitor as taught by Hirose for the capacitor in the memory system of Blodgett et al. in order to provide an improved capacitor with large capacity. As a result, the modified Blodgett et al. provides a capacitor comprising a first conductive capacitor plate formed of a first material; a second conductive capacitor plate; a metal oxide layer and a metal layer interposed between said first and second conductive capacitor plates.

Regarding claims 82 and 109, the metal oxide layer 14A comprises titanium.

Regarding claim 84, the second conductive capacitor plate is formed of metal.

Regarding claim 110, the capacitor further comprises a diffusion barrier layer 14 interposed between the first conductive capacitor plate 13 and the metal oxide layer 14A.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien Tran whose telephone number is (703) 308-4108. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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August 28, 2003

Thien Tran Patent Examiner

Technology Center 2800